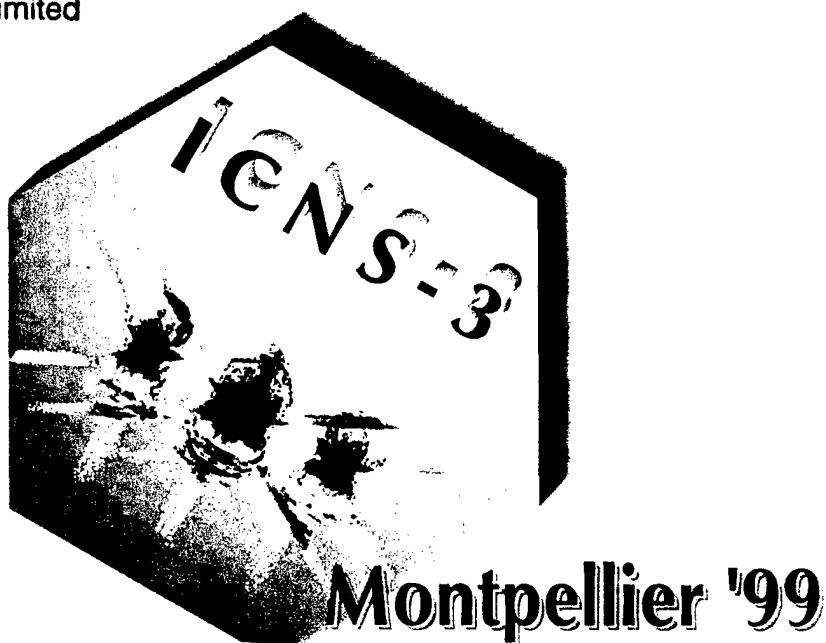


**The Third International Conference
on
Nitride Semiconductors**

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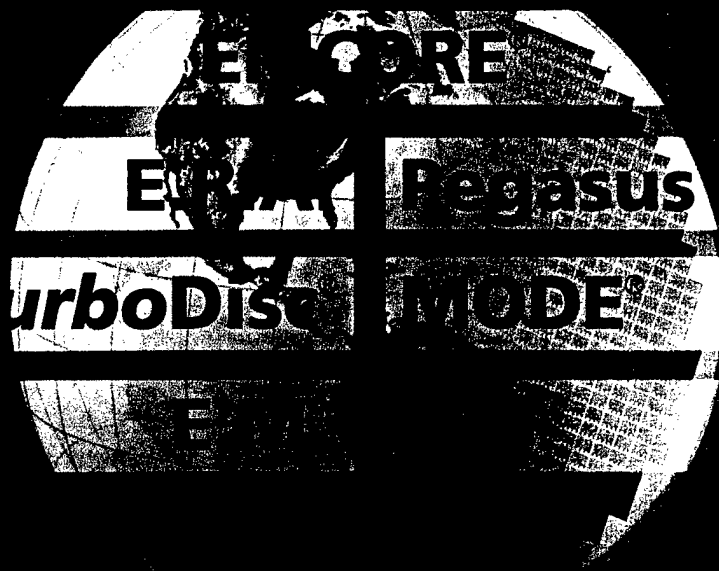


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Montpellier, France
July 4-9, 1999

PROGRAMME

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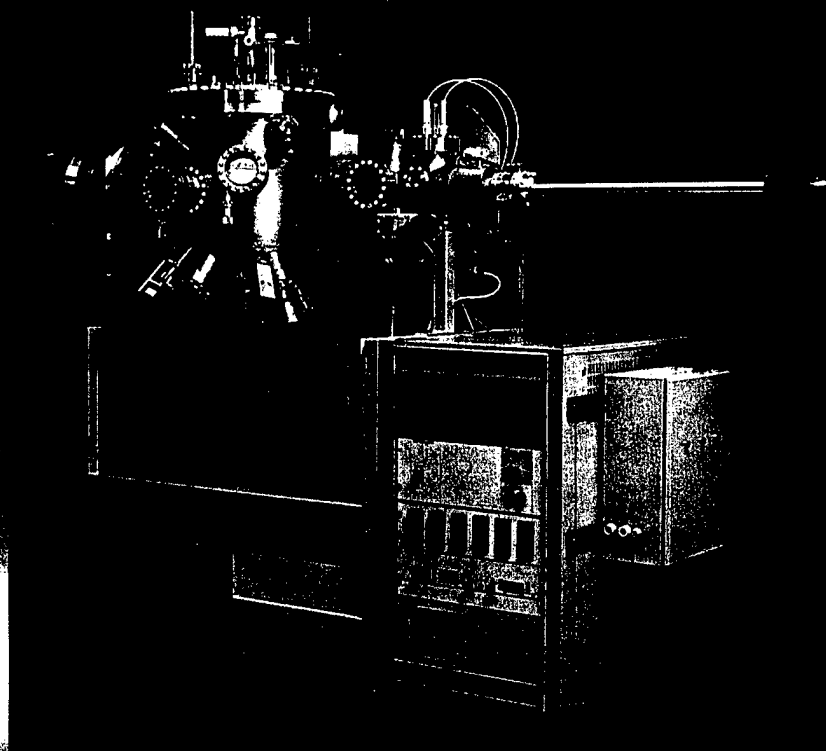
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**GALLIUM NITRIDE AND RELATED COMPOUNDS
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GENERAL PROGRAMME

Sunday July 4th, 1999

15.00-19.00 REGISTRATION

Monday July 5th, 1999

08.00 Registration
09.00-09.30 OPENING SESSION - Room : PASTEUR
09.30-10.30 Conferences
10.30-11.00 OPENING OF THE EXHIBITION - COFFEE BREAK
11.00-12.30 Working session
12.30-14.30 LUNCH BREAK
14.30-16.45 Working session
16.45-18.45 POSTER SESSION I - COFFEE BREAK (*offered by EMCORE Corp.*)
19.00 WELCOMING COCKTAIL - Room : SALON CENTRAL Level 3
*Offered by Mr. Georges FRECHE, Member of Parliament and Mayor of Montpellier,
and the local council*

Tuesday July 6th, 1999

08.30-10.30 Working session
10.30-11.00 VISIT OF THE EXHIBITION - COFFEE BREAK
11.00-12.30 Working session
12.30-14.30 LUNCH BREAK
14.30-16.45 Working session
16.45-18.45 POSTER SESSION II - COFFEE BREAK (*offered by RIBER S.A.*)
18.45 Round table

Wednesday July 7th, 1999

08.30-10.45 Working session
10.45-11.15 VISIT OF THE EXHIBITION - COFFEE BREAK
11.15-12.30 Special session in honour of Professor AKASAKI
12.30-14.30 LUNCH BREAK
14.30-16.45 Working session
16.45-18.45 POSTER SESSION III - COFFEE BREAK (*offered by EPICHEM LTD.*)
18.45 CONCERT - Room : PASTEUR

Thursday July 8th, 1999

08.30-10.30 Working session
10.30-11.00 VISIT OF THE EXHIBITION - COFFEE BREAK
11.00-12.30 Working session
12.30-14.30 LUNCH BREAK
14.30-17.00 Working session
19.15 Departure by bus for the VALMAGNE ABBEY
Meeting place : "Parvis" of the Convention Centre (in front of the level 3 Entrance, side Esplanade)
20.00 CONFERENCE BANQUET (*for registered persons*)

Friday July 9th, 1999

08.30-10.30 Working session
10.30-11.00 VISIT OF THE EXHIBITION - COFFEE BREAK (*offered by AXTRON AG*)
11.00-12.15 Working session
12.15 CLOSING SESSION

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Monday July 5th, 1999

Session sponsored by PICO GIGA

09:00 OPENING SESSION

- 09:30 Mo_01 GALLIUM NITRIDE AS SEEN BY THE INDUSTRY
Jean Yves Duboz*
- 10:00 Mo_02 PRESENT STATUS OF InGaN-BASED LEDs AND LASER DIODES
Shuji Nakamura*

Session sponsored by EMCORE Corp.

- 11:00 Mo_03 INFLUENCE OF InGaN INHOMOGENEITY ON NITRIDE LASERS
K. Domen*, A. Kuramata, R. Soejima, S. Kubota, K. Horino, T. Tanahashi
- 11:30 Mo_04 EFFECT OF THE CONFINEMENT LAYER DESIGN ON THE LUMINESCENCE OF
InGaN/GaN SINGLE QUANTUM WELLS
S. Keller, S. B. Fleischer, S. F. Chichibu, J. E. Bowers, U. K. Mishra, S. P. DenBaars
- 11:45 Mo_05 COMPARISON OF InGaN/GaN QUANTUM WELLS GROWN ON SAPPHIRE AND
BULK GaN SUBSTRATES
S. Sakai, T. Sugahara, Q. Fareed, S. Tottori, M. Lachab, T. Wang
- 12:00 Mo_06 INVESTIGATION OF THE OPTICAL PROPERTIES IN InGaN/GaN MULTIPLE QUANTUM WELLS
AND SINGLE QUANTUM WELL
T. Wang, D. Nakagawa, M. Lachab, T. Sugahara, S. Sakai
- 12:15 Mo_07 COMPARISON OF OPTICAL PROPERTIES BETWEEN GaN AND InGaN QUANTUM WELLS
P. Riblet, H. Hirayama, A. Kinoshita, A. Hirata, T. Sugano, Y. Aoyagi

Session sponsored by AIXTRON AG

- 14:30 Mo_08 PRESSURE STUDIES OF DEFECTS AND IMPURITIES IN NITRIDES
T. Suski*
- 15:00 Mo_09 THE EFFECT OF DOPING AND GROWTH STOICHIOMETRY ON THE PROPERTIES
OF THREADING EDGE DISLOCATION IN GaN
A.F. Wright*, K. Leung
- 15:30 Mo_10 INVESTIGATIONS ON THE V-DEFECT FORMATION IN GaInN-GaN MULTI QUANTUM
WELL STRUCTURES
J. Off, F. Scholz, A. Kniest, O. Gfrörer, A. Hangleiter, G. Brockt, H. Lakner
- 15:45 Mo_11 STIMULATED EMISSION AND THE MOTT TRANSITION IN GaN EPILAYERS UNDER
HIGH-DENSITY EXCITATION
R.A. Taylor, S. Hess, K. Kyhm, J.F. Ryan, G.P. Yablonskii, E.V. Lutsenko,
V.N. Pavlovskii, M. Heuken
- 16:00 Mo_12 PHOTOLUMINESCENCE INTENSITY AND SPECTRAL DISTRIBUTION OF GaN FILMS
ON SiC SUBSTRATES THE DEPENDENCE ON DISLOCATION DENSITY AND STRUCTURE
P. Hacke, A. Kuramata, K. Domen, T. Tanahashi
- 16:15 Mo_13 CHARACTERISATION OF GALLIUM NITRIDE DEVICE STRUCTURES USING TRANSMISSION
ELECTRON MICROSCOPY
D.M. Tricker, A.N. Bright, C.J. Humphreys
- 16:30 Mo_14 CATHODOLUMINESCENCE DETERMINATION OF STRAIN-INDUCED SHIFTS AT
MICROCRACKS IN GaN/AlGaIN MULTI QUANTUM WELLS
C.E. Norman, R.A. Hogg, A.J. Shields, N. Lizuka

POSTER SESSION 1

Tuesday July 6th

Session sponsored by CREE Research Inc.

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|-------|-------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| 8:30 | Tu_01 | ROLE OF POLARIZATION INDUCED EFFECTS IN GROUP III NITRIDE BASED DEVICES
O. Ambacher*, L.F. Eastman, M. Stutzmann |
| 9:00 | Tu_02 | SPONTANEOUS POLARIZATION VERSUS PIEZOELECTRIC FIELD EFFECTS IN III-V NITRIDES
Fabio Bernardini*, Vincenzo Fiorentini |
| 9:30 | Tu_03 | STARK-LIKE LADDER IN PIEZOELECTRIC GaInN/GaN QUANTUM WELLS
C. Wetzel, T. Takeuchi, H. Amano, I. Akasaki |
| 9:45 | Tu_04 | DIRECT OBSERVATION OF PYROELECTRIC FIELDS IN InGaN/GaN AND AlGaIn/GaN HETEROSTRUCTURES
O. Gfrörer, J. Off, F. Scholz, A. Hangleiter |
| 10:00 | Tu_05 | SCATTERING, RECOMBINATION AND PIEZOELECTRICITY AT DISLOCATIONS IN GROUP III-NITRIDES
M. Albrecht, S. Christiansen, T. Remmele, H.P. Strunk, A. Cremades, G. Salviati, H. Banzhoff, H. Lichte |
| 10:15 | Tu_06 | INTRINSIC INFRARED LUMINESCENCE FROM InGaN LAYERS
K.P. O'Donnell, R.W. Martin, S. Pereira, A. Bangura, M.E. White, W. Van der Stricht, K. Jacobs |

Session sponsored by RIBER S.A.

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| 11:00 | Tu_07 | EPITAXIAL GROWTH OF GAN, AlN AND InN: 2D/3D TRANSITION AND SURFACTANT EFFECTS
B. Daudin*, G. Feuillet |
| 11:30 | Tu_08 | MOCVD GROWTH AND OPTICAL CHARACTERIZATION OF STACKED InGaN QUANTUM DOTS FOR LASER APPLICATIONS
K. Tachibana, T. Someya, Y. Arakawa |
| 11:45 | Tu_09 | GaN QUANTUM STRUCTURES WITH FRACTIONAL DIMENSIONS - FROM QUANTUM WELL TO QUANTUM DOT
Satoru Tanaka, Ikuo Suemune, Peter Ramvall, Yoshinobu Aoyagi |
| 12:00 | Tu_10 | OPTICAL PROPERTIES OF STRUCTURES WITH SINGLE AND MULTIPLE InGaN INSERTIONS IN A GaN MATRIX
A.V. Sakharov, W.V. Lundin, I.L. Krestnikov, V.A. Semenov, A.S. Usikov, A.F. Tsatsul'nikov, Yu.G. Musikhin, M.V. Baidakova, Zh.I. Alferov, N.N. Ledentsov, A. Hoffmann, D. Bimberg |
| 12:15 | Tu_11 | In ON GaN SURFACES: ALLOY FORMATION, ORDERING AND SURFACTANT BEHAVIOR
J. Neugebauer, T. Zywietz, M. Scheffler, J. Northrup |

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|-------|-------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| 14:30 | Tu_12 | OPTICAL SPECTROSCOPY OF InGaN/GaN QUANTUM WELLS
E. Berkowicz, D. Gershoni*, G. Bahir, A.C. Abare, S.P. Denbaars, L.A. Coldren |
| 15:00 | Tu_13 | MOLECULAR BEAM EPITAXY OF NITRIDE BASED QW STRUCTURES
N. Grandjean*, J. Massies |
| 15:30 | Tu_14 | PROPERTIES OF QUANTUM WELL EXCITONS IN GaN/AlGaIn AND InGaIn/GaN/AlGaIn UV, BLUE, GREEN, AND AMBER LIGHT EMITTING DIODE STRUCTURES
S.F. Chichibu, T. Deguchi, T. Sota, S.P. DenBaars, S. Nakamura |
| 15:45 | Tu_15 | DYNAMICS OF EXCITONS IN GaN-AlGaIn MULTIPLE QUANTUM WELLS WITH VARYING DEPTHS, THICKNESSES AND BARRIER LAYERS
P. Lefebvre, M. Gallart, T. Taliercio, B. Gil, J. Allègre, H. Mathieu, N. Grandjean, M. Leroux, J. Massies, P. Bigenwald |
| 16:00 | Tu_16 | BAND FILLING AND ENERGY RELAXATION IN InGaIn/GaN-MULTIPLE QUANTUM WELL STRUCTURES
T. Riemann, D. Rudloff, J. Christen, A. Krost, M. Lünenbürger, H. Protzmann, M. Heuken |
| 16:15 | Tu_17 | HIGH-RESOLUTION PHOTOLUMINESCENCE AND REFLECTANCE SPECTRA OF HOMOEPITAXIAL GaN-LAYERS
K. Kornitzer, T. Ebner, M. Grehl, K. Thonke, R. Sauer, C. Kirchner, V. Schwegler, M. Kamp, M. Leszczynski, I. Grzegory, S. Porowski |
| 16:30 | Tu_18 | TEMPORARY DYNAMICS OF EXCITON-POLARITONS IN GaN FILMS
G. Malpuech, A.V. Kavokin |

POSTER SESSION 2

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| 18:45 | Round table - sponsored by EMCORE Corp. |
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Thursday July 8th

Session sponsored by CNRS

- 8:30 Th_01 ANOMALOUS BEHAVIOR OF NITRIDE ALLOYS
A. Zunger*
- 9:00 Th_02 LATTICE DYNAMICS OF TERNARY ALLOYS
Friedhelm Bechstedt*
- 9:30 Th_03 ENERGY BAND/LATTICE MISMATCH ENGINEERING IN QUATERNARY AlInGaN/GaN HETEROSTRUCTURE
M. Asif Khan, J.W. Yang, G. Simin, Hans zur Loye, R. Bicknell-Tassius, R. Gaska, M.S. Shur, G. Tamulaitis, A. Zukauskas
- 9:45 Th_04 MOVPE GROWTH AND LUMINESCENCE PROPERTY OF GaAsN ALLOYS WITH HIGHER NITROGEN CONCENTRATIONS
K. Onabe, D. Aoki, J. Wu, H. Yaguchi, Y. Shiraki
- 10:00 Th_05 MECHANISM FOR LIGHT EMISSION IN GaNAs/GaAs STRUCTURES GROWN BY MOLECULAR BEAM EPITAXY
I.A. Buyanova, W.M. Chen, P.N. Hai, B. Monemar, H. Xin, C. W. Tu
- 10:15 Th_06 MOVPE GROWTH OF In-RICH In_xGa_{1-x}N (0.5 ≤ x ≤ 1) FILMS ON α-Al₂O₃(0001)
A. Yamamoto, Y. Nakagawa, T. Sugiura, A. Hashimoto

Session sponsored by University Montpellier II

- 11:00 Th_07 CONDUCTION BAND ENERGY SPECTRUM OF TWO DIMENSIONAL ELECTRONS IN GaN/AlGaN HETEROJUNCTIONS
W. Knap*, E. Frayssinet, C. Skierbiszewski, C. Chaubet, M.L. Sadowskia, D. Maude, M. Asif Khan, M.S. Shur
- 11:30 Th_08 RECORD HIGH MOBILITY AlGaIn/GaN HETEROSTRUCTURES BASED ON OPTIMIZATION OF GaN BY MBE
B. Heying, C. Elsass, I. Smorchkova, T. Mates, E. Haus, P. Fini, S.P. DenBaars, U. Mishra, J.S. Speck
- 11:45 Th_09 GROWTH OF HIGH MOBILITY AlGaIn/GaN HETEROSTRUCTURES BY AMMONIA-MOLECULAR BEAM EPITAXY
James B. Webb, H. Tang, J. Bardwell
- 12:00 Th_10 ENHANCED TWO-DIMENSIONAL ELECTRON GAS CONFINEMENT EFFECT ON TRANSPORT PROPERTIES IN AlGaIn/InGaIn/AlGaIn DOUBLE-HETEROSTRUCTURES
N. Maeda, T. Saitoh, K. Tsubaki, T. Nishida, N. Kobayashi
- 12:15 Th_11 WURTZITE GaN SURFACE RECONSTRUCTIONS STUDIED BY STM
T. Sakurai, Q.K. Xue, Q.Z. Xue, Y. Hasegawa, I.S.T. Tsong, T. Ohno

Session sponsored by RENISHAW Ltd.

- 14:30 Th_12 GROWTH AND CHARACTERIZATION OF HIGH-EFFICIENCY InGaIn MQW BLUE AND GREEN LEDS FROM LARGE-SCALE PRODUCTION MOCVD REACTORS
C.A. Tran*, R.F. Karlicek Jr., M.G. Brown, I. Eliashevich, A. Whitcomb, A. Gurary, R. Saito
- 15:00 Th_13 MULTIWAFFER PLANETARY REACTORS FOR THE PRODUCTION OF GaN BASED COMPOUNDS
M. Heuken*
- 15:30 Th_14 HETEROEPITAXY OF DOPED AND UNDOPE D CUBIC III-NITRIDES
D.J. As*, K.Lischka
- 16:00 Th_15 MICROSTRUCTURE OF CUBIC AND HEXAGONAL GaN GROWN ON SAPPHIRE (0001) BY ECR-MBE WITH VARIOUS ELECTRIC BIASES
T. Araki, T. Minami, Y. Nanishi
- 16:15 Th_16 THE INFLUENCE OF STRUCTURAL PROPERTIES ON THE MECHANISMS OF OPTICAL AMPLIFICATION IN CUBIC InGaIn
J.Chr. Holst, A. Hoffmann, I. Broser, F. Bertram, T. Riemann, J. Christen, D.J. As, D. Schikora, B. Schoettker, K. Lischka
- 16:30 Th_17 COMPREHENSIVE INVESTIGATION ON THE MIXING AND REACTING BEHAVIORS OF PRECURSORS DURING METAL ORGANIC VAPOR PHASE EPITAXY OF GALLIUM NITRIDE
T.F. Kuech, Jingxi Sun, K.S. Boutros, J.M. Redwing
- 16:45 Th_18 GROWTH OF HIGH QUALITY Ga-POLAR GaN LAYERS ON GaN SUBSTRATES AFTER NOVEL REACTIVE ION ETCHING
J.L. Weyhe, A. Zauner, P.D. Brown, F. Karouta, A. Wysmolek, P.R. Hageman, S. Porowski

Wednesday July 7th

Session sponsored by NICHIA Chemical Industries

- 8:30 **We_01** STATUS OF NITRIDE BASED EMITTERS ON SiC.
K. Doverspike, H. Dieringer, D. Emerson, K. Habereran, D. Slater, H.S. Kong, G.E. Bulman, J. Edmond
- 9:00 **We_02** CW OPERATION OF AlGaInN-GaN LASER DIODES
T. Asano, K. Yanashima, T. Asatsuma, T. Hino, T. Yamaguchi, S. Tomiya, T. Kobayashi, M. Ikeda
- 9:30 **We_03** FABRICATION AND CHARACTERIZATION OF GaN-BASED LASER DIODE GROWN ON THICK N-AlGaIn CONTACT LAYER
T. Takeuchi, T. Detchprohm, M. Yano, M. Yamaguchi, N. Hayashi, M. Iwaya, K. Isomura, K. Kimura, H. Amano, I. Akasaki, Yw. Kaneko, S. Watanabe, Y. Yamaoka, R. Shioda, T. Hidaka, Ys. Kaneko, N. Yamada
- 9:45 **We_04** CONTINUOUS-WAVE OPERATION OF INGAN MULTI-QUANTUM-WELL LASER DIODES GROWN ON AN N-GAN SUBSTRATE WITH A BACKSIDE N-CONTACT
M. Kuramoto, C. Sasaoka, Y. Hisanaga, A. Kimura, A.A. Yamaguchi, H. Sunakawa, N. Kuroda, M. Nido, A. Usui, M. Mizuta
- 10:00 **We_05** RECOMBINATION DYNAMICS IN In_xGa_{1-x}N MULTIPLE-QUANTUM-WELL BASED LASER DIODES UNDER HIGH PHOTO-EXCITATION
Yukio Narukawa, Yoichi Kawakami, Shigeo Fujita, Shuji Nakamura
- 10:15 **We_06** 346 nm EMISSION FROM AlGaIn MULTI-QUANTUM-WELL LIGHT EMITTING DIODE
T. Nishida, N. Kobayashi
- 10:30 **We_14** ROOM-TEMPERATURE CONTINUOUS-WAVE OPERATION OF INGAN MULTIPLE QUANTUM WELL LASER DIODES WITH AN ASYMMETRIC WAVEGUIDE STRUCTURE
Michael Kneissl, David P. Bour, Chris G. Van de Walle, Linda T. Romano, John E. Northrup, Rose M. Wood, Mark Teepe, Noble M. Johnson
- 11:15 **SPECIAL SESSION IN HONOUR OF PROFESSOR AKASAKI**

Session sponsored by Thomas Swan & Co. Ltd.

- 14:30 **We_07** MOCVD GROWTH OF GROUP-III NITRIDE BASED HETEROSTRUCTURES FOR HIGH POWER, HIGH FREQUENCY ELECTRONICS
S. Den Baars, U. Mishra, C. Chen, G. Parish, S. Keller, Y.F. Wu, D. Kapolnek, B. Keller
- 15:00 **We_08** RESULTS, POTENTIAL AND CHALLENGES OF HIGH POWER GAN-BASED TRANSISTORS
Lester F. Eastman
- 15:30 **We_09** FIRST DEMONSTRATION OF AlGaIn/GaN DUAL-GATE MODULATION-DOPED FIELD-EFFECT TRANSISTORS
C.H. Chen, K. Krishnamurthy, Y.F. Wu, S. Keller, G. Parish, M. Rodwell, Steven P. Denbaars, U.K. Mishra
- 15:45 **We_10** DC AND RF CHARACTERIZATION OF AlN/GaN HFETs
I. Daumiller, P. Schmid, C. Kirchner, M. Kamp, L. Pond, K.J. Ebeling, C. Weitzel, E. Kohn
- 16:00 **We_11** AlGaIn/GaN HFETs WITH NEW OHMIC AND SCHOTTKY CONTACTS FOR THERMAL STABILITY UP TO 400°C
J. Hilsenbeck, W. Rieger, E. Nebauer, G. Tränkle, J. Würfl, A. Ramakrishnan, H. Obloh
- 16:15 **We_12** SCHOTTKY BARRIER PHOTODETECTOR ON EPITAXIAL LATERAL OVERGROWN GaN
E. Monroy, F. Calle, E. Muñoz, B. Beaumont, F. Omnès, P. Gibart
- 16:30 **We_13** REDUCTION OF OHMIC CONTACT RESISTIVITY ON P-TYPE GAN BY SURFACE TREATMENT
J.L. Lee, J.K. Kim, J.W. Lee, Y.J. Park, T. Kim

POSTER SESSION 3

18:45 **CONCERT**

Friday July 9th

Session sponsored by Thomson-CSF

- 8:30 Fr_01 RECENT PROGRESS IN SELECTIVE AREA GROWTH AND EPITAXIAL LATERAL OVERGROWTH OF III-NITRIDES
K. Hiramatsu*, H. Miyake, A. Motogaito, H. Sone, Y. Kawaguchi, N. Sawaki, Y. Lyeckika, T. Maeda
- 9:15 Fr_02 PENDEO-EPITAXY VS. LATERAL EPITAXIAL OVERGROWTH OF GaN - A COMPARATIVE STUDY
Tsuetanka S. Zheleva, Wael M. Ashmawi, Kenneth A. Jones, Darren Thomson, Thomas Gehrke, Kevin Linthicum, Robert F. Davis
- 9:30 Fr_03 SELECTIVE AREA GROWTH OF GaN ON STRIPE-PATTERNED (111) Si SUBSTRATE BY METALORGANIC VAPOR PHASE EPITAXY
Y. Kawaguchi, Y. Honda, M. Yamaguchi, N. Sawaki, K. Hiramatsu
- 9:45 Fr_04 TEM STUDY OF THE BEHAVIOUR OF DISLOCATIONS DURING ELOG GaN GROWTH
V. Bousquet, P. Vennéguès, B. Beaumont, P. Gibart
- 10:00 Fr_05 SELECTIVE GROWTH OF CUBIC GaN ON PATTERNED GaAs (100) SUBSTRATES BY METALORGANIC VAPOR PHASE EPITAXY
Jun Wu, Masahiro Kudo, Akira Nagayama, Ryuji Katayama, Hiroyuki Yaguchi, Kentaro Onabe, Yasuhiro Shiraki
- 10:15 Fr_06 STRUCTURAL, OPTICAL, AND ELECTRICAL PROPERTIES OF GaN LATERALLY OVERGROWN ON Si(111) SUBSTRATES FOR DEVICE APPLICATIONS
H. Marchand, N. Zhang, J.P. Ibbetson, L. Zhao, B. Moran, Y. Golan, S.J. Rosner, G. Girolami, P.T. Fini, S. Keller, J.S. Speck, S.P. DenBaars, U.K. Mishra

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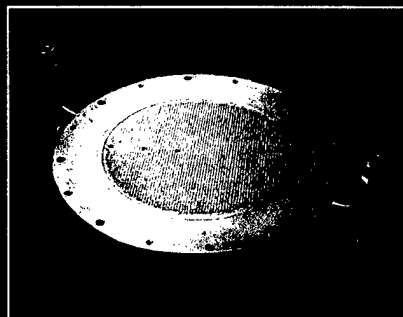
- 11:00 Fr_07 DEFECT AND STRESS CONTROL IN GROUP III NITRIDES USING LOW TEMPERATURE INTERLAYERS
H. Amano*, M. Iwaya, N. Hayashi, T. Kashima, T. Takeuchi, C. Wetzel, I. Akasaki, J. Han, S. Hearne, J.A. Floro, E. Chason, J. Figiel
- 11:30 Fr_08 GaN/SiC QUASI-SUBSTRATES FOR GaN-BASED LEDs
C. Kirchner, V. Schwegler, M. Kamp, K.J. Ebeling, Yu. Melnik, A. Nikolaev, D. Tsvetkov, V. Dmitriev
- 11:45 Fr_09 GaN SUBSTRATES: GROWTH and CHARACTERIZATION
Olga Kryliouk, Michael Reed, Michael Mastro, Timothy Anderson, Bruce Chai
- 12:00 Fr_10 GaN ON Si(111): FROM GROWTH OPTIMIZATION TO OPTICAL PROPERTIES OF QUANTUM WELL STRUCTURES
F. Semond, B. Damilano, S. Vézian, N. Grandjean, M. Leroux, J. Massies
- 12:15 CLOSING SESSION

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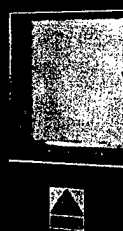
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POSTER SESSION 1

Monday July 5th

- Mo_P001** THE GaN GROWTH BY A HOT FILAMENT METALORGANIC VAPOR PHASE DEPOSITION TECHNIQUE
T. Boufaden, A. Rebey, I. Halidou, Z. Chine, B. El Jani
- Mo_P002** NEW PRETREATMENT OF SAPPHIRE FOR GaN DEPOSITION
Dongjin Byun, Hyun-Jeong Kim, Chang Hee Hong, Gyeungho Kim, Dong-Wha Kum
- Mo_P003** MULTIPARAMETER STATISTICAL DESIGN OF EXPERIMENTS FOR GaN GROWTH OPTIMIZATION
A. Hass Bar-Ilan, S. Zamir, O. Katz, B. Meyler, J. Salzman
- Mo_P004** THICK HYDRIDE VAPOUR PHASE EPITAXIAL GaN LAYERS GROWN ON A-PLANE SAPPHIRE WITH DIFFERENT BUFFERS
T. Paskova, E. Goldys, J. Birch, E.B. Svedberg, P. Runesson, S. Tungasmita, B. Monemar
- Mo_P005** MOCVD GROWTH OF CUBIC GALLIUM NITRIDE : THE EFFECT OF THE V/III RATIO
M. Moret, S. Ruffenach-Clur, N. Moreaud, O. Briot, J. Calas, R.L. Aulombard
- Mo_P006** RHEED STUDIES OF GROUP III NITRIDES GROWN BY MBE
C.T. Foxon, C.S. Davis, S.V. Novikov, O.H. Hughes
- Mo_P007** THICK GaN GROWTH ON GaAs (111) SUBSTRATES AT 1000°C WITH HVPE
F. Hasegawa, M. Minami, K. Sunaba, T. Suemasu
- Mo_P008** EXPERIMENTAL AND THEORETICAL STUDY OF THE GROWTH OF GaN ON SAPPHIRE BY HVPE
A. Trassoudaine, E. Aujol, P. Disseix, D. Castelluci, R. Cadoret
- Mo_P009** GROWTH CONTROL OF CUBIC GaN AND CUBIC GaInN (GaAlN) ALLOYS BY RHEED OSCILLATIONS
E. Martinez-Guerrero, B. Daudin, G. Feuillet, H. Mariette, P. Aboughe-nze, Y. Monteil, A. Philippe, C. Bru-Chevallier
- Mo_P010** GROWTH AND CHARACTERISATION OF GALLIUM NITRIDE FILMS PRODUCED BY LOW TEMPERATURE REACTIVE SPUTTERING
W.T. Young, S.R.P. Silva, M. Kuball, J.V. Anguita, J.M. Shannon, K.P. Homewood, B.J. Sealy
- Mo_P011** QUANTUM CHEMICAL STUDIES OF GAS PHASE REACTIONS BETWEEN TMA, TMG, TMI AND NH₃
A. Tachibana, K. Nakamura, O. Makino, H. Tokunaga, N. Akutsu, K. Matsumoto
- Mo_P012** MBE GROWTH OF HEXAGONAL InN FILMS ON SAPPHIRE WITH DIFFERENT INITIAL GROWTH STAGES
V.V. Mamutin, V.A. Vekshin, V.Yu. Davydov, V.V. Ratnikov, T.V. Shubina, V.V. Emtsev, S.V. Ivanov, P.S. Kop'ev
- Mo_P013** Mg-DOPED HEXAGONAL InN/Al₂O₃ FILMS GROWN BY MBE
V.V. Mamutin, V.A. Vekshin, V.Yu. Davydov, V.V. Ratnikov, Yu. Kudriavtsev, B.Ya. Ber, V.V. Emtsev, S.V. Ivanov
- Mo_P014** GROWTH AND OPTICAL CHARACTERIZATION OF ALUMINUM NITRIDE ALLOYS WITH HIGH ALUMINUM-CONTENTS
J. Y. Lin, R. Mair, J. Li, H.S. Kim, H.X. Jiang
- Mo_P015** 2.6µm/hr HIGH-SPEED GROWTH OF GaN BY RF-MOLECULAR BEAM EPITAXY AND IMPROVEMENT OF CRYSTAL QUALITY BY MIGRATION ENHANCED EPITAXY
Daisuke Sugihara, Akihiko Kikuchi, Kazuhide Kusakabe, Shinichi Nakamura, Yousuke Toyoura, Takayuki Yamada, Katsumi Kishino
- Mo_P016** EPITAXIAL GROWTH OF GaN, AlN AND ZnO THIN FILMS ON SAPPHIRE SUBSTRATE BY SINGLE TARGET OFF-AXIS SPUTTERING
S.W. Kim, N. Kamata, S. Hino, T. Kodama, H. Hirose, T. Yamada*, T. Suzuki
- Mo_P017** LOW-TEMPERATURE SYNTHESIS OF GALLIUM NITRIDE THIN FILMS USING REACTIVE RF-MAGNETRON SPUTTERING
V. Bondar, I. Kucharsky, B. Simkiv, Yu. Dubov, S. Popovich
- Mo_P018** PREFERENTIAL GROWTH MODE OF CUBIC GaN BY METALORGANIC MOLECULAR BEAM EPITAXY ON SAPPHIRE (0001) SUBSTRATES
J. Suda, T. Kurobe, T. Masuda, H. Matsunami
- Mo_P019** GROWTH AND CHARACTERIZATION OF THICK AlGaIn EPILAYERS DOPED WITH Si GROWN ON SAPPHIRE SUBSTRATES
W.V. Lundin, A.S. Usikov, A.V. Sakharov, V.V. Tretyakov, D.V. Poloskin
- Mo_P020** INFLUENCE OF AMBIENT GAS ON THE EPITAXIAL LATERAL OVERGROWTH OF GaN BY METALORGANIC VAPOR PHASE EPITAXY
Y. Kawaguchi, S. Nambu, M. Yamaguchi, N. Sawaki, H. Miyake, K. Hiramatsu, K. Tsukamoto, N. Kuwano, K. Oki

Mo_P021	MOVPE GROWTH OF HIGH QUALITY CUBIC GaN ON GaAs - THE ROLE OF GROWTH RATES AND BUFFER LAYER STRUCTURES M. Funato, M. Ogawa, T. Ishido, Sz. Fujita, Sg. Fujita
Mo_P022	MBE GROWTH OF AUTODOPED GaN USING A THIN AlN INTERMEDIATE LAYER J. Stemmer, H. Klausning, D. Mistele, T. Rotter, O. Semchinova, J. Aderhold, J. Graul
Mo_P023	EPITAXY OF GALLIUM NITRIDE BY HVPE USING LOW TEMPERATURE INTERMEDIATE BUFFER LAYERS DEPOSITED BY MOCVD V. Wagner, O. Parillaud, H.J. Bühlmann, M. Illegems
Mo_P024	IN SITU MONITORING OF GAN GROWTH IN MULTIWAFFER MOVPE REACTORS M. Heuken, H. Protzmann, M. Luenenbuerger, H. Juergensen
Mo_P025	Mg-INDUCED KINETICAL CHANGES IN THE GROWTH OF CUBIC AND HEXAGONAL GaN BY MOLECULAR BEAM EPITAXY Guido Mula, Bruno Daudin, Philippe Peyla
Mo_P026	SUBLIMATION GROWTH OF AlN S.Yu. Karpov, D.V. Zimina1, Yu.N. Makarov, E.N. Mokhov, A.D. Roenkov, M.G. Ramm, Yu.A. Vodakov
Mo_P027	MODELING STUDY OF HYDRIDE VAPOR PHASE EPITAXY OF GaN S.Yu. Karpov, D.V. Zimina, Yu.N. Makarov, B. Beaumont, J. Nataf, P. Gibart, M. Heuken, H. Juergensen, A. Krishnan
Mo_P028	MOCVD EPITAXY ON FREE-STANDING HVPE-GaN SUBSTRATES R. Miskys, M.K. Kelly, O. Ambacher, M. Stutzmann
Mo_P029	INTERFACE TREATMENT OF GaN/InGaN-MULTI QUANTUM WELL STRUCTURES GROWN IN PRODUCTION TYPE MOVPE SYSTEMS M. Heuken, M. Luenenbuerger, J. Blaesing, A. Krost, H. Protzmann
Mo_P030	ON THE ORIGINS OF LOW INDIUM INCORPORATION DURING MOVPE OF InGaN Yu.N. Makarov, R.A. Talalaev, E.V. Yakovlev, S.Yu. Karpov, I.Yu. Evstratov, A.N. Vorob'ev
Mo_P031	GROWTH AND EVAPORATION KINETICS OF GaN IN AMMONIA ATMOSPHERE S.Yu. Karpov, R.A. Talalaev, Yu.N. Makarov, N. Grandjean, J. Massies
Mo_P032	MECHANISM OF CHEMICAL VAPOUR DEPOSITION OF GALLIUM NITRIDE FILMS BASED ON PYROLYSIS OF AMMONIA HALIDES COMPLEXES S.E. Alexandrov, D.M. Krasovitskiy
Mo_P033	INFLUENCE OF THE GaN SEED LAYER AND GROWTH PARAMETERS ON SELECTIVE EPITAXY OF GaN BY HVPE O. Parillaud, V. Wagner, H.J. Bühlmann, M. Illegems
Mo_P034	A TWO STEP METHOD FOR EPITAXIAL LATERAL OVERGROWTH OF GaN B. Beaumont, V. Bousquet, P. Vennéguès, M. Vaille, A. Bouillé, P. Gibart, S. Dassonneville, A. Amokrane, B. Sieber
Mo_P035	REMOTE PLASMA MOCVD GROWTH AND PROCESSING OF GaN BY REAL TIME ELLIPSOMETRY M. Losurdo, P. Capezzuto, G. Bruno
Mo_P036	PROPERTIES OF HOMOEPITAXIAL AND HETEROEPITAXIAL GaN LAYERS GROWN BY PLASMA-ASSISTED MBE M.A. Sánchez-García, F.B. Naranjo, J.L. Pau, A. Jiménez, E. Calleja, E. Munoz, S.I. Molina, A.M. Sánchez, F.J. Pacheco, R. García
Mo_P037	SURFACTANT EFFECT OF As ON THE GROWTH OF GaN ON Si(111) SUBSTRATES BY PLASMA ASSISTED MBE A. Jiménez, M.A. Sánchez-García, F.B. Naranjo, J.L. Pau, E. Calleja, E. Munoz, S.I. Molina, A.M. Sánchez, F.J. Pacheco, R. García
Mo_P038	GROWTH OF AlGaIn ON Si(111), Al ₂ O ₃ (0001) AND GaN(0001) BY PLASMA-ASSISTED MBE F.B. Naranjo, J.L. Pau, A. Jiménez, M.A. Sanchez-García, E. Calleja, E. Muñoz
Mo_P039	STRUCTURE OF AlN AND GaN BULK CRYSTAL GROWN BY HVPE M. Albrecht, H.P. Strunk, Yu. Melnik, A. Nikolaev, I. Nikitina, V. Dmitriev, F. Demangeot, J. Frandon, M. Renucci
Mo_P040	SUPPRESSION OF THE HEXAGONAL PHASE IN CUBIC GaN FILMS BY USING MISORIENTED GaAs (001) SUBSTRATES A. Nagayama, R. Katayama, N. Nakadan, K. Miwa, H. Yaguchi, J. Wu, K. Onabe, Y. Shiraki
Mo_P041	STRAIN RELAXATION IN GAN FILMS AS A FUNCTION OF GROWTH DIRECTION AND BUFFER LAYER MEASURED BY RAMAN SPECTROSCOPY R. Seitz, T. Monteiro, E. Pereira, M. Di Poisson-Forte
Mo_P042	GROWTH OF POLYCRYSTALLINE GaN ON SILICON(001) SUBSTRATES BY RF PLASMA CHEMICAL VAPOR DEPOSITION WITH ZnO BUFFER LAYER D.C. Park, Sz. Fujita, Sg. Fujita
Mo_P043	THE APPLICATION OF LOW TEMPERATURE GaN BUFFER LAYER ON ZnO/Si SUBSTRATE TO OBTAIN THICK FILMS OF HIGH QUALITY GaN J.W. Lee, S.W. Park, H.S. Paek, J.B. Yoo, P.W. Yu

- Mo_P044** GROWTH OF BULK AlN BY PHYSICAL VAPOR TRANSPORT
Tim Housain, V. Dmitriev, P. Zhou, H.N. Jayathirtha, M.G. Spencer, V. Dimitriev, Yu Melnik, A. Nikolaev
- Mo_P045** LOW TEMPERATURE GROWTH OF GaN ON a-Al₂O₃ AND Si SUBSTRATE USING AN ATOMIC NITROGEN SOURCE BASED ON DIELECTRIC BARRIER DISCHARGE
Dongjin Byun, Joosung Kim, Jin-Sang Kim, Dong-Wha Kum
- Mo_P046** MOCVD GROWTH OF GaN ON LiAlO₂ (100) SUBSTRATES
Ke Xu, Peizhen Deng, Zujie Fang, Jun Xu
- Mo_P047** MIXING MECHANISM OF h-GaN IN c-GaN GROWTH ON GaAs (001) SUBSTRATES
A. Hashimoto, H. Wada, T. Ueda, A. Masuda, A. Yamamoto
- Mo_P048** GROWTH OF BORON NITRIDE THIN FILMS ON SILICON SUBSTRATES USING NEW ORGANOBORON PRECURSORS
Jin-Hyo Boo, Carsten Rohr, Wilson Ho
- Mo_P049** GROWTH OF AlN AND GaN THIN FILMS ON Si(100) USING NEW SINGLE MOLECULAR PRECURSORS BY MOCVD METHOD
J.H. Boo, S.B. Lee, Y.S. Kim, J.T. Park, K.S. Yu, Y. Kim
- Mo_P050** CHARACTERISTICS OF OPTICALLY-PUMPED FREE STANDING GaN GROWN BY HYDRIDE VAPOR PHASE EPITAXY
S.T. Kim, K.Y. Park, M.H. Lee, D.C. Moon, J.K. Kim, Y.H. Choi, T.K. Yoo
- Mo_P051** INFLUENCE OF GROWTH CONDITION ON QUALITY OF GaN, AlN AND AlGaIn GROWN ON SiC AND SAPPHIRE BY RF-PLASMA ASSISTED MOLECULAR BEAM EPITAXY
Ming Qi, Aizhen Li, Wei Li, Zhibiao Zhao, Yonggang Zhang
- Mo_P052** PHOTOLUMINESCENCE AND GAIN OF MBE GROWN CUBIC In_xGa_{1-x}N/GaN HETEROSTRUCTURES
T. Frey, D.J. As, D. Schikora, K. Lischka, J. Holst, A. Hoffmann
- Mo_P053** A COMPARATIVE STUDY OF MOVPE GROWTH OF InN ON GaAs(111) SUBSTRATES USING A NITRIDED OR GROWN GaN BUFFER LAYER
A. Yamamoto, T. Arita, M. Adachi, T. Sugiura, A. Hashimoto
- Mo_P054** EFFECT OF HYDROGEN ON GROWTH BEHAVIOR OF GaN DURING REMOTE PLASMA ENHANCED METALORGANIC CHEMICAL VAPOR DEPOSITION
M.H. Kim, H.J. Kim, H. Na, F. Qi, E. Yoon
- Mo_P055** CLASSICAL AND QUANTUM SIMULATIONS OF In AND Al INCORPORATION IN GaN
J.A. Chisholm, P. D. Bristowe
- Mo_P056** HIGH-QUALITY GaN ON Si SUBSTRATE BY USE OF AlGaIn/GaN INTERMEDIATE LAYER
H. Ishikawa, Z.Y. Zhao, N. Nakada, T. Egawa, T. Soga, T. Jimbo, M. Umeno
- Mo_P057** GAS PHASE STUDIES OF TRIMETHYLGALLIUM WITH AMMONIA, PROPYLAMINE AND WATER AT ELEVATED TEMPERATURES: TOWARDS AN UNDERSTANDING OF GaN GROWTH AND OXYGEN INCORPORATION
U. Bergmann, V. Reimer, B. Atakan
- Mo_P058** HOMOEPITAXIAL GROWTH AND LUMINESCENCE CHARACTERIZATION OF GaN EPILAYER BY RF-MBE ON MOCVD-GROWN GaN SUBSTRATE
S. Kurai, S. Kubo, T. Okazaki, S. Manabe, T. Sugita, A. Kawabe, Y. Yamada, T. Taguchi
- Mo_P059** INFLUENCE OF THE GROWTH CONDITIONS ON THE SURFACE MORPHOLOGY AND STRUCTURE OF MBE GROWN AlN
L. Kirste, M. Rattunde, J. Portmann, R. Brenn, K.W. Benz, D.G. Ebling, K. Tillmann
- Mo_P060** INFLUENCE OF MBE GROWTH TEMPERATURE ON THE PROPERTIES OF CUBIC GaN GROWN DIRECTLY ON GaAs SUBSTRATES
A. Georgakilas, M. Androulidaki, K. Tsagaraki, K. Amimer, G. Constantinidis, N.T. Pelekanos
- Mo_P061** POSSIBILITY OF STRAIN CONTROL IN AlN LAYER GROWN BY MOVPE ON (0001)6H-SiC WITH GaN/AlN BUFFER
H. Kawanishi, M. Kurimoto, T. Nakada, Y. Ishihara, M. Shibata, T. Takano, J. Yamamoto, T. Honda
- Mo_P062** CHARACTERIZATION OF AlGaIn/GaN HETEROSTRUCTURES GROWN BY METALORGANIC CHEMICAL VAPOR DEPOSITION
R.D. Dupuis, C.J. Eiting, D.J.H. Lambert, H.K. Kwon, B.S. Shelton, M.M. Wong, T.G. Zhu, D.E. Lin
- Mo_P063** X-RAY PHOTOELECTRON SPECTROSCOPIC INVESTIGATION OF THE GaAs NITRIDATION MECHANISM WITH AN ECR PLASMA SOURCE
M. Sauvage-Simkin, Y. Garreau, A. Barski, R. Langer, F. Bruno, L. Floreano, R. Gotter, A. Morgante, A. Santaniello, D. Svetko, A. Verdini
- Mo_P064** OPTIMIZATION OF Si/N TREATMENT TIME OF SAPPHIRE SURFACE AND ITS EFFECT ON THE MOVPE GaN OVERLAYERS
S. Haffouz, B. Beaumont, P. Vennéguès, P. Gibart
- Mo_P065** PLASMA-ASSISTED MBE GROWTH OF GaN ON HVPE-GaN AND SAPPHIRE SUBSTRATES
A. Rinta-Möykky, P. Laukkanen, S. Lehtonen, S. Laaksonen, J. Likonen, P. Uusimaa, M. Pessa

- Mo_P066** PROCESS OPTIMISATION OF THE REACTIVE ION ETCHING OF GALLIUM NITRIDE IN METHYLCHLORIDE/HYDROGEN USING THE ORTHOGONAL DESIGN METHOD
M. Dineen, H. Thomas, B. Humphreys, S.G. McMeekin
- Mo_P067** STUDIES OF GaN HOMOEPITAXY WITH LOW-ENERGY ELECTRON MICROSCOPY
I.S.T. Tsong, A. Pavlovskaya, V.M. Torres, E. Bauer, R.B. Doak, D.B. Thomson, R.F. Davis
- Mo_P068** RAMAN SCATTERING STUDY OF ZINC BLENDE $\text{In}_x\text{Ga}_{1-x}\text{N}$ ALLOYS
A. Tabata, E. Silveira, J.R. Leite, A.P. Lima, L.M.R. Scolfaro, V. Lemos, T. Frey, D.J. As, D. Schikora, K. Lischka
- Mo_P069** EFFECT OF ANNEALING ON DEFECTS IN AS-GROWN AND γ -RAY IRRADIATED n-GaN LAYERS
N. Shmidt, V. Emtsev, I. Krestnikov, W. Lundin, A. Osinsky, D. Poloskin, A. Sakharov, A. Usikov
- Mo_P070** PHASE SEPARATION AND ORDERING CO-EXISTING IN MOCVD $\text{In}_x\text{Ga}_{1-x}\text{N}$
M.K. Behbehani, E.L. Piner, X. Liu, N.A. El-Masry, S.M. Bedair
- Mo_P071** MOCVD GROWTH AND CHARACTERIZATION OF GaN FILMS WITH COMPOSITE INTERMEDIATE LAYER BUFFER ON Si SUBSTRATE
X. Zhang, S.J. Chua, Z.C. Feng, J. Chen, J. Lin
- Mo_P072** THE NATURE OF NATIVE DEFECTS IN GaN THIN FILMS
V. Bondar, V. Vasylytsiv, I. Kucharsky, Yu. Dubov
- Mo_P073** DETERMINING OF STRESSES IN GaN THIN FILMS BY X-RAY DIFFRACTION ANALYSIS
L. Axelrud, V. Bondar, V. Davydov, I. Kucharsky
- Mo_P074** MICROSTRUCTURAL ANALYSIS OF POST-ANNEALED AlN NUCLEATION LAYERS
Y.M. Le Vaillant, R. Bisaro, P. Vennéguès, P. Galtier, J.Y. Duboz, B. Gil, S. Ruffenach-Clur, O. Briot, R.L. Aulombard
- Mo_P075** IN-EDGE X-RAY ABSORPTION FINE STRUCTURE OF INN AND INGAN FILMS
K.P. O'Donnell, R.W. Martin, M.E. White, J.F.W. Mosselmans, Qixin Guo
- Mo_P076** SPECTROSCOPIC IMAGING OF InGaN LAYERS
K.P.O'Donnell, C. Trager Cowan, S. Pereira, A. Bangura, C. Young, M.E. White, M.J. Tobin
- Mo_P077** COMPOSITION ANALYSIS USING ERD
L. Görgens, G. Dollinger, A. Bergmaier, O. Ambacher, L. Eastman, R. Dimitrov, A. Mitschel
- Mo_P078** THE ATOMIC STRUCTURE OF THREADING DISLOCATIONS FROM LOW-ANGLE TO HIGH-ANGLE GRAIN BOUNDARIES IN GaN/SAPPHIRE EPITAXIAL LAYERS
V. Potin, G. Nouet, P. Ruterana, R.C. Pond
- Mo_P079** SELF-ARRANGED LAYER STACKING SEQUENCE WITH SIX-BILAYER PERIODICITY ALONG THE $\langle 111 \rangle$ DIRECTION IN GaN ON GaAs
M. Funato, T. Ishido, Sz. Fujita, Sg. Fujita
- Mo_P080** DEFECT-SELECTIVE ETCHING OF GaN
J.L. Weyher, G. Nowak, P.D. Brown, J.L. Rouvière, A. Presz, I. Grzegory
- Mo_P081** STRAIN DISTRIBUTION IN GaN HEXAGONS MEASURED BY RAMAN SPECTROSCOPY
R. Seitz, T. Monteiro, E. Pereira, M. Di Poisson-Forte
- Mo_P082** MICRO DEFECTS IN NEARLY DISLOCATION FREE GaN DOPED WITH Mg DURING HIGH PRESSURE CRYSTALLIZATION
S. Porowski, J. Kozubowski, J. Borysiuk, J.L. Weyher, M. Bockowski, B. Lucznik, I. Grzegory
- Mo_P083** INVESTIGATION OF GaN THIN FILMS BY HIGH RESOLUTION DOUBLE CRYSTAL X- RAY DIFFRACTION
D. Johnston, T. Lafford, G. Fraser, N. Loxley
- Mo_P084** DEFECT CREATION AND ANNIHILATION IN III-N LAYERS ON GaN SINGLE CRYSTALS AND ON SAPPHIRE
M. Leszczynski, P. Prystawko, T. Suski, E. Frayssinet, J. Domagala, G. Nowak, I. Grzegory, M. Bockowski, S. Porowski
- Mo_P085** HRTEM EVALUATION OF GaN LATERALLY OVERGROWN ON HVPE AlN/6H-SiC
P. Ruterana, B. Beaumont, P. Gibart, Yu. Melnik
- Mo_P086** ANALYSIS OF THE DEFECT STRUCTURE OF EPITAXIAL GaN LAYERS
H. Heinke, V. Kirchner, S. Einfeldt, D. Hommel
- Mo_P087** ORIGIN OF THE TILT OF CRYSTALLINE AXIS IN TERMS OF THE STRUCTURAL PROPERTY IN CUBIC GaN EPILAYER ON (001) GaAs SUBSTRATE GROWN BY RF-MBE
H. Hayashi, A. Hayashida, A.W. Jia, M. Kobayashi, M. Shimotomai, Y. Kato, A. Yoshikawa, K. Takahashi
- Mo_P088** IN-SITU Er-DOPING OF GaN AND THE EFFECT OF SURFACE MORPHOLOGY AND ROOM-TEMPERATURE PHOTOLUMINESCENCE
J.M. Zavada, M.E. Overberg, J. Brand, J.D. MacKenzie, C.R. Abernathy, S.J. Pearton, R.G. Wilson
- Mo_P089** GaN LAYERS GROWN ON Si(111) SUBSTRATES WITH AlN BUFFER LAYERS: A SCANNING TUNNELING MICROSCOPY INVESTIGATION IN AIR
R. Rinaldi, S. Antonaci, R. Cingolani, A. Botchkarev, H. Morkoç

Mo_P090	THERMODYNAMIC ANALYSIS ON THE MOVPE GROWTH OF NITRIDE SEMICONDUCTORS USING HYDRAZINE A. Koukitu, Y. Kumagai, H. Seki, N. Kubota
Mo_P091	SURFACE ENERGIES AND SURFACE DIPOLES AT III-NITRIDE(111) SURFACES IN DEPENDENCE ON STOICHIOMETRY J. Furthmüller, U. Grossner, F. Bechstedt
Mo_P093	AB INITIO CALCULATION OF VIBRATIONAL PROPERTIES OF CUBIC AND HEXAGONAL InN H.W. Leite Alves, J.L.A. Alves, A. Tabata, L.M.R. Scolfaro, J.R. Leite
Mo_P094	POLARIZATION EFFECTS ON SCHOTTKY BARRIER IN GaN-METAL JUNCTIONS P. Ruggerone, F. Bernardini, D. Mura, V. Fiorentini
Mo_P095	STUDY OF PHASE-SEPARATED THIN LAYERS OF INGAN GROWN BY METALORGANIC-VAPOR-PHASE-EPITAXY P. Li, G. Li, S.J. Chua, W. Wang, X.C. Wang, Y.P. Guo
Mo_P096	EVOLUTION WITH TEMPERATURE OF THE STRAIN STATE OF GaN THIN LAYERS GROWN ON DIFFERENT SUBSTRATES E. Deleporte, C. Guénaud, M. Voos, B. Beaumont, P. Gibart, H. Larèche
Mo_P097	PHOTOLUMINESCENCE INVESTIGATIONS OF AlGaIn ON GaN EPITAXIAL FILMS B.K. Meyer, G. Steude, H. Amano, I. Akasaki
Mo_P098	PHONONS IN HEXAGONAL InN. EXPERIMENT AND THEORY V.Yu. Davydov, A.A. Klochikhin, M.B. Smirnov, V.V. Emtsev, V.D. Petrikov, I.A. Abroyan, I.N. Goncharuk, A.N. Smirnov, V.V. Mamutin, S.V. Ivanov, T. Inushima
Mo_P099	INFRARED PHOTOLUMINESCENCE AND EPR IN BULK GaN CRYSTALS HEAVILY DOPED WITH Cr AND V I.V. Ilyin, R.A. Babunts, P.G. Baranov, E.N. Mokhov, V.A. Khramtsov
Mo_P100	OBSERVATION OF PHONON MODES IN BULK InGaIn FILMS BY RAMAN SCATTERING H. Harima, Y. Sone, E. Kurimoto, S. Nakashima, S. Chu, A. Ishida, H. Fujiyasu
Mo_P101	LOCAL VIBRATIONAL MODES IN p-TYPE GaN OBSERVED BY RAMAN SCATTERING H. Harima, T. Inoue, Y. Sone, S. Nakashima, M. Ishida, M. Taneya
Mo_P102	DISLOCATION NATURE OF GROWTH HILLOCKS IN HOMOEPITAXIAL MOCVD GaN LAYERS G. Nowak, K. Pakula, I. Grzegory, J.L. Weyher, S. Porowski
Mo_P103	OXYGEN-RELATED DEFECTS AND ENERGY ACCUMULATION IN ALUMINIUM NITRIDE CERAMICS B. Berzina, L. Trinkler, J. Sils, E. Palcevskis, P.Christensen
Mo_P104	REAL-TIME X-RAY SCATTERING STUDIES OF SURFACE STRUCTURE AND GROWTH MODES DURING MOCVD GROWTH OF GaN G.B. Stephenson, A. Munkholm, J.A. Eastman, C. Thompson, P. Fini, J.S. Speck, O. Auciello, S.P. DenBaars
Mo_P105	HIGH QUALITY GaN LAYERS GROWN BY MOCVD ON Si(111) – SUBSTRATES A. Strittmatter, A. Krost, D. Bimberg



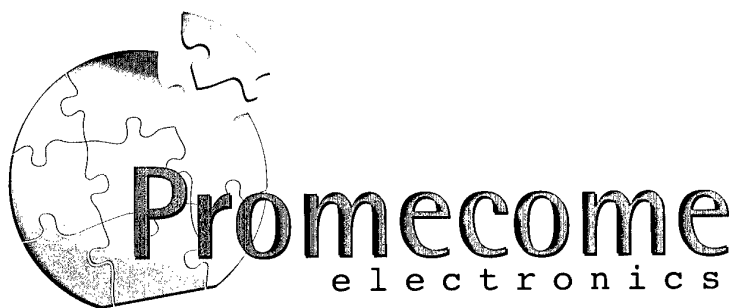
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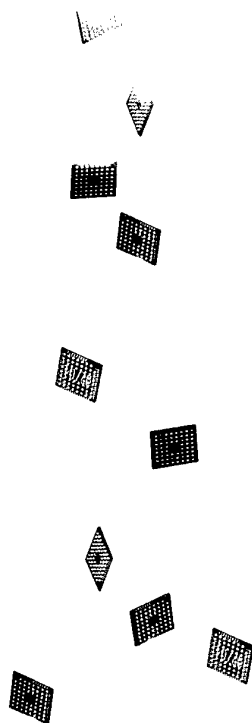
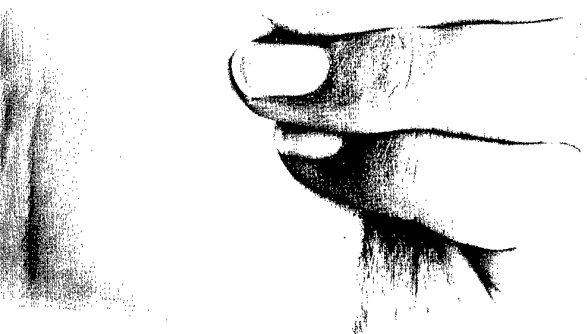
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POSTER SESSION 2

Tuesday July 6th

- Tu_P001** SOLID INCORPORATION OF AlGa_N AND INFLUENCE OF GROWTH INTERRUPTION ON GaN/AlGa_N QUANTUM WELL STRUCTURES GROWN BY MOCVD
G.M. Yang, S.C. Choi, J.H. Kim, J.Y. Choi, K.J. Lee, K.Y. Lim, H.J. Lee
- Tu_P002** METALORGANIC MOLECULAR BEAM EPITAXY OF In_xGa_{1-x}N FOR A VISIBLE SPECTRAL RANGE IN PHOTOLUMINESCENCE
Seong-Ju Park, Min-Ho Kim, Jun-Kyu Cho
- Tu_P003** PROPERTIES OF NANOCRYSTALLINE GALLIUM NITRIDE THIN FILMS GROWN ON MONOCRYSTALLINE SUBSTRATES AND BUFFER LAYERS
V. Bondar
- Tu_P004** GROWTH AND OPTICAL CHARACTERIZATION OF In_xGa_{1-x}N DOTS RESULTING FROM A 2D-3D TRANSITION
C. Adelmann, J. Simon, N. Pelekanos, Y. Samson, G. Feuillet, B. Daudin
- Tu_P005** InGa_N/Ga_N MQW AND Mg-DOPED Ga_N GROWTH USING A SHUTTER CONTROL METHOD BY RF-MOLECULAR BEAM EPITAXY
Shinichi Nakamura, Akihiko Kikuchi, Koichi Kushi, Hajime Sasamoto, Daisuke Sugihara, Kazuhide Kusakabe, Katsumi Kishino
- Tu_P006** ENHANCED BLUE-LIGHT EMISSION FROM InGa_N/Ga_N QUANTUM WELLS GROWN OVER A MULTILAYERED BUFFER ON SILICON SUBSTRATE BY METAL ORGANIC CHEMICAL VAPOR DEPOSITION
Xiong Zhang, Soo-Jin Chua, Wei Liu
- Tu_P007** GROWTH AND CHARACTERIZATION OF THICK GaAs_N EPILAYERS AND GaInNAs/GaAs MULTIQUANTUM WELLS
Ph. Gilet, A. Chenevas-Paule, Ph. Duvaut, L. Grenouillet, A. Million
- Tu_P008** THE STRUCTURE OF InGa_N LAYERS AND QUANTUM WELLS GROWN BY MOCVD
P. Ruterana, C. Gonthrin, F. Mascle, R. Aguinet, M.A. Poisson, W. Van der Stricht
- Tu_P009** GROWTH AND RELAXATION OF Ga_N/AlGa_N HETEROSTRUCTURES GROWN BY MBE ON PRESSURE GROWN GaN(0001) SUBSTRATES
M. Albrecht, H.P. Strunk, C.T. Foxon, D. Korakakis, I. Grzegory, S. Porowski
- Tu_P010** INFLUENCE OF STRAIN AND THERMAL ANNEALING EFFECTS ON BANDGAP INHOMOGENEITY OF InGa_N MQW
K. Domen, A. Kuramata, T. Tanahashi
- Tu_P011** IMPROVEMENT OF SURFACE MORPHOLOGY IN InGa_N MULTIPLE QUANTUM WELL STRUCTURE
J. Gotoh, K. Uchida, A. Niwa, S. Gotoh, T. Yang, J. Kasai, T. Mishima
- Tu_P012** DISLOCATIONS IN Ga_N and Ga_N/Al_N HETEROSTRUCTURES
J.L. Rouvière, B. Daudin, G. Feuillet, J.L. Weyher
- Tu_P013** CONTROL OF SPATIAL FLUCTUATIONS IN InGa_N/Ga_N QUANTUM WELLS BY MOLECULAR BEAM EPITAXY GROWTH
S. Einfeldt, T. Bottcher, D. Rudloff, T. Riemann, F. Bertram, H. Selke, J. Christen, P.L. Ryder, D. Hommel
- Tu_P014** STRUCTURAL DEFECTS OF CUBIC InGa_N/Ga_N HETEROSTRUCTURES GROWN ON GaAs (001) SUBSTRATES BY MOVPE
Y. Taniyasu, Y. Watanabe, D. H. Lim, A.W. Jia, M. Shimotomai, Y. Kato, M. Kobayashi, A. Yoshikawa, K. Takahashi
- Tu_P015** TIME-RESOLVED SPECTROSCOPY OF InGa_N LIGHT-EMITTING DIODES, MULTIPLE QUANTUM WELLS, AND THIN FILMS
Frederick H. Long, M. Pophristic, C. Tran, R.F. Karlicek Jr., I.T. Ferguson
- Tu_P016** INHOMOGENEOUS BROADENING OF EXCITONS IN THIN FILMS OF Ga_N : EFFECT ON THE TIME RESOLVED TRANSMISSION SPECTRA
A.V. Kavokin, G. Malpuech, G. Panzarini
- Tu_P017** OPTICAL PROPERTIES OF HEXAGONAL Ga_N CRYSTALS WITH IMPURITIES AND DEFECTS
P. Tronc, Yu.E. Kitaev, G. Wang, M.F. Limonov, G.Neu
- Tu_P018** EXTENDED TIGHT BINDING AND THERMOCHEMICAL MODELING OF III-NITRIDE HETEROSTRUCTURES AS A FUNCTION OF TEMPERATURE, STRAIN, AND PRESSURE
Hilmi Ünlü
- Tu_P019** CALCULATION OF EXCITON ENERGIES FOR SELF-FORMED INGAN QUANTUM DOTS
R.W. Martin, K.P. O'Donnell

Tu_P020	OPTICAL PROPERTIES OF GaN (110) AND (1010) SURFACES Cecilia Noguez, R. Esquivel-Sirvent
Tu_P021	STRAIN INFLUENCE ON III-NITRIDES: AB INITIO STUDIES OF STRUCTURAL, LATTICE-DYNAMICAL, AND DIELECTRIC PROPERTIES J.M. Wagner, F. Bechstedt
Tu_P022	RELAXATION EFFECTS ON THE NEGATIVELY CHARGED Mg IMPURITY IN ZINC BLENDE GaN L.M.R. Scolfaro, L.K. Teles, J.R. Leite, A. Tabata, D.J.As
Tu_P023	INFLUENCE OF INTERNAL POLARIZATION FIELDS ON THE DISORDER BROADENING OF EXCITONS IN (In,Ga)N/GaN QUANTUM WELLS O. Mayrock, H.J. Wünsche, F. Henneberger, O. Brandt
Tu_P024	EFFECTS OF MACROSCOPIC-POLARIZATION INDUCED ELECTROSTATIC FIELDS IN III-V NITRIDE MULTI-QUANTUM-WELLS Vincenzo Fiorentini, Fabio Bernardini, A. Di Carlo, F. Della Sala, P. Lugli
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Tu_P026	TWO-PHOTON ABSORPTION IN GaAlN NANOCRYSTALLITES EMBEDDED WITHIN PHOTOPOLYMER MATRICES A. Mefleh, S. Benet, S. Brunet, M. Malachowski, I.V. Kityk
Tu_P027	TEMPERATURE DEPENDENCE OF HEXAGONAL-GaN OPTICAL PROPERTIES BELOW THE BANDGAP L. Sizade, S. Colard, M. Mihailovic, J. Leymarie, A. Vasson, N. Grandjean, M. Leroux, J. Massies
Tu_P028	TEMPERATURE DEPENDENCE OF PHOTOLUMINESCENCE INTENSITIES IN UNDOPEd AND DOPED GaN M. Leroux, N. Grandjean, B. Beaumont, G. Nataf, F. Sémond, J. Massies, P. Gibart
Tu_P029	OBSERVATION OF QUANTUM DOT/QUANTUM WIRE-LIKE PROPERTIES IN THE PHASE-SEPARATED GaN-RICH GaNP R. Kuroiwa, H. Asahi, K. Iwata, H. Tampo, K. Asami, S. Gonda
Tu_P030	OPTICAL CONSTANTS OF Al _x Ga _{1-x} N: MODELING OVER A WIDE SPECTRAL RANGE A.B. Djurišić, E.H. Li
Tu_P031	STRAINED InGa _N /Ga _N QUANTUM WELLS CHARACTERISED BY ROOM-TEMPERATURE PHOTOLUMINESCENCE AND SPECTROSCOPIC ELLIPSOMETRY A. Ramakrishnan, J. Wagner, H. Obloh, M. Kunzer
Tu_P032	DYNAMICS OF THE BOUND EXCITONS IN GaN EPILAYERS GROWN BY HYDRIDE VAPOR PHASE EPITAXY G. Pozina, J.P. Bergman, T. Paskova, B. Monemar
Tu_P033	OPTICAL AND STRUCTURAL CHARACTERIZATION OF Ga(In) _N THREE-DIMENSIONAL NANOSTRUCTURES GROWN BY PLASMA ASSISTED MOLECULAR BEAM EPITAXY G. Pozina, J.P. Bergman, B. Monemar, V.V. Mamutin, V.A. Vekshin, S.V. Ivanov, T.V. Shubina, A.A. Toropov
Tu_P034	HOT CARRIER RELAXATION BY EXTREME ELECTRON – LO PHONON SCATTERING IN GaN S. Hess, R.A. Taylor, E.D. O'Sullivan, J.F. Ryan, N.J. Cain, V. Roberts, J.S. Roberts
Tu_P035	FEMTOSECOND EXCITON DYNAMICS AND THE MOTT TRANSITION IN GaN UNDER RESONANT EXCITATION R.A. Taylor, S. Hess, K. Kyhm, J.F. Ryan, B. Beaumont, P. Gibart
Tu_P036	VIOLET TO ORANGE ROOM TEMPERATURE LUMINESCENCE FROM GaN QUANTUM DOTS ON Si(111) SUBSTRATES B. Damilano, N. Grandjean, F. Semond, J. Massies, M. Leroux
Tu_P037	CHARACTERIZATION OF InGa _N SINGLE LAYERS AND QUANTUM WELLS GROWN BY LP-MOVPE B. Schineller, P.H. Lim, O. Schön, H. Protzmann, M. Heuken, K. Heime
Tu_P038	IMPACT IONIZATION OF EXCITONS IN AN ELECTRIC FIELD IN GaN D.K. Nelson, M.A. Jacobson, V.D. Kagan, N. Shmidt
Tu_P039	CRYSTAL FILMS CHARACTERIZATION BY URBACH SPECTRAL TAIL OF ABSORPTION FOR GALLIUM NITRIDE M.A. Jacobson, O.V. Konstantinov, D.K. Nelson, S.O. Romanovskii, Z. Hatzopoulos, A. Georgakilas
Tu_P040	INFLUENCE OF THE ELECTRIC FIELD ON THE EXCITONIC SPECTRA OF EPITAXIAL GaN FILMS M.A. Jacobson, E.V. Kalinina, D.K. Nelson, S.O. Romanovskii, A.V. Sel'kin

- Tu_P041** OPTICAL STUDY OF CUBIC GALLIUM NITRIDE BAND-EDGE AND RELATION WITH RESIDUAL STRAIN
A. Philippe, C. Bru-Chevallier, H. Gamez-Cuatzin, G. Guillot, E. Martinez-Guerrero, G. Feuillet, B. Daudin, P. Aboughe'Nze, Y. Monteil
- Tu_P042** OPTICAL PROPERTIES OF AN AlInN INTERFACE LAYER SPONTANEOUSLY FORMED IN HEXAGONAL InN/ SAPPHIRE HETEROSTRUCTURES
T.V. Shubina, V.V. Mamutin, V.A. Vekshin, V.V. Ratnikov, A.A. Toropov, S.V. Ivanov, M. Karlsteen, U. Södervall, M. Willander, G.R. Pozina, B. Monemar
- Tu_P043** HIGH-TEMPERATURE LASING IN InGaN/GaN MULTIQUANTUM WELL HETEROSTRUCTURES
I.P. Marko, E.V. Lutsenko, V.N. Pavlovskii, G.P. Yablonskii, O. Schön, H. Protzman, M. Lünenbürger, M. Heuken, B. Schineller, K. Heime
- Tu_P044** RED LUMINESCENCE OF Mg-DOPED GaN
M.W. Bayerl, M.S. Brandt, E.R. Glaser, A.E. Wickenden, D.D. Koleske, R.L. Henry, M. Stutzmann
- Tu_P045** EXCITATION DENSITY DEPENDENCE OF PHOTOLUMINESCENCE AND BARRIER DOPING EFFECT IN $\text{In}_x\text{Ga}_{1-x}\text{N}$ QUANTUM WELLS
Eunsoon Oh, C.S. Sone, Hyeongsoo Park, O.H. Nam, Yongjo Park
- Tu_P046** INFRARED REFLECTANCE INVESTIGATION OF UN-DOPED AND Si-DOPED GaN FILMS ON SAPPHIRE
Z.C. Feng, Y.T. Hou, M.F. Li, S.J. Chuua, W. Wang, L. Zhu
- Tu_P047** OPTICAL BAND GAP DEPENDENCE ON THICKNESS AND COMPOSITION OF $\text{In}_x\text{Ga}_{1-x}\text{N}$ GROWN ON GAN
C.A. Parker, M.J. Reed, J.C. Roberts, S.X. Liu, N.A. El-Masry, S.M. Bedair
- Tu_P048** OPTICAL CHARACTERIZATION OF CUBIC AlGaIn EPILAYERS BY CATHOOLUMINESCENCE AND SPECTROSCOPIC ELLIPSOMETRY
H. Okumura, T. Koizumi, Y. Ishida, H. Yaguchi, S. Yoshida, S. Chichibu
- Tu_P049** STRUCTURAL AND OPTICAL ANALYSIS OF (IN,GA)N STRUCTURES GROWN BY MOCVD
D. Rudloff, J. Bläsing, T. Riemann, J. Christen, A. Krost, M. Lünenbürger, H. Protzmann, M. Heuken
- Tu_P050** NEAR-BAND GAP SELECTIVE PHOTOLUMINESCENCE IN WURTZITE GaN
G. Neu, M. Teisseire, B. Beaumont, P. Gibart
- Tu_P051** TIME-RESOLVED PHOTOLUMINESCENCE OF CUBIC GaN GROWN BY METALORGANIC VAPOR PHASE EPITAXY
H. Yaguchi, J. Wu, H. Akiyama, M. Baba, K. Onabe, Y. Shiraki
- Tu_P052** PHOTOLUMINESCENCE EXCITATION SPECTRUM STUDY ON $\text{GaN}/\text{Al}_{0.15}\text{Ga}_{0.85}\text{N}$ MQWS
T. Nishida, M. Kumagai, H. Ando, N. Kobayashi
- Tu_P053** HOT ELECTRONS AND HOLES IN HIGHLY PHOTOEXCITED GaN EPILAYERS
A. Zukauskas, G. Tamulaitis, R. Gaska, M.S. Shur, M.A. Khan, J.W. Yang
- Tu_P054** FINITE-TEMPERATURE BAND-GAP RENORMALIZATION IN HIGHLY PHOTOEXCITED GaN EPILAYERS
A. Zukauskas, S. Jursenas, G. Kurilcik, G. Tamulaitis, M.S. Shur, R. Gaska, J.W. Yang, M.A. Khan
- Tu_P055** InGaN/GaN/AlGaIn VERTICAL CAVITY SURFACE EMITTING LASER OPERATING AT ROOM TEMPERATURE AT OPTICAL PUMPING
I.L. Krestnikov, W.V. Lundin, A.V. Sakharov, V.A. Semenov, A.S. Usikov, A.F. Tsatsul'nikov, N.N. Ledentsov, A. Hoffmann, Zh.I. Alferov, D. Bimberg
- Tu_P056** AN INVESTIGATION INTO THE ORIGIN OF THE 3.424 eV PEAK IN THE LOW TEMPERATURE PHOTOLUMINESCENCE OF GaN GROWN BY MOLECULAR BEAM EPITAXY
A. Bell, C.T. Foxon, I. Harrison, T. Cheng, D. Korakakis, S. Novikov, B. Ya Ber, Y.A. Kudriavtsev
- Tu_P057** GREEN EMISSION FROM Tb-DOPED GaN GROWN BY MOVPE
Kazuhiko Hara, Nobuyuki Ohtake
- Tu_P058** EXCITONIC THERMALIZATION, TRANSPORT AND RECOMBINATION IN HOMOEPITAXIAL ALLIUM NITRIDE
K.P. Korona, J. Kuhl, J.M. Baranowski, S. Porowski
- Tu_P060** FAR-INFRARED REFLECTIVITY INVESTIGATIONS ON GaN SINGLE CRYSTALS AND HOMOEPITAXIAL LAYERS
E. Frayssine, W. Knap, P. Prystawko, M. Leszczynski, B. Beaumont, T. Suski, P. Wisniewski, E. Litwin-Staszewska, S. Porowski
- Tu_P061** A STUDY ON THE SILANE DOPING OF HETERO-EPITAXIAL MOCVD GROWN GaN
P.R. Hageman, M.A.C. Devillers, A.R.A. Zauner, V. Kirilyuk, W.S. Bouwens, R.C.M. Crane, P.K. Larsen
- Tu_P062** DETERMINATION OF OPTICAL CONSTANTS FOR CUBIC $\text{In}_x\text{Ga}_{1-x}\text{N}$
R. Goldhahn, J. Scheiner, S. Shokhovets, T. Frey, U. Köhler, D. As

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Tu_P064	FREE-CARRIER AND CRYSTAL-STRUCTURE PROPERTIES OF GROUP III-NITRIDE HETEROSTRUCTURES MEASURED BY INFRARED ELLIPSOMETRY M. Schubert, J.A. Woollam, A. Kassig, B. Rheinländer, J. Off, F. Scholz
Tu_P065	EVIDENCE FOR SPONTANEOUS POLARIZATION EFFECTS IN GaN/AlGaN QUANTUM WELLS J. Simon, R. Langer, A. Barski, N.T. Pelekanos
Tu_P066	IMPROVEMENT OF THE SPATIALLY INHOMOGENEOUS OPTICAL PROPERTIES OF GaN FILMS BY INDIUM DOPING DURING GAS-SOURCE MOLECULAR BEAM EPITAXY Ken-ichi Hoshi, Satoru Tanaka, Hidekazu Kumano, Ikuo Suemune, Xu-Qiang Shen, Peter Ramvall, Yoshinobu Aoyagi
Tu_P067	POLARISED MAGNETOLUMINESCENCE OF EXCITONS IN HOMOEPITAXIAL GaN LAYERS A. Wysmolek, M. Potemski, R. Stepniewski, J. Lusakowski, K. Pakula, J.M. Baranowski, G. Martinez, P. Wyder, I. Grzegory, S. Porowski
Tu_P068	MAGNETO-OPTICS OF BULK GALLIUM NITRIDE P.A. Shields, R.J. Nicholas, B. Beaumont, P. Gibart
Tu_P069	THE OPTICAL PROPERTIES AND RESIDUAL STRAIN OF THICK GaN FILMS WITH DIFFERENT THICKNESS USING PHOTOLUMINESCENCE (PL) AND PHOTOREFLECTANCE (PR) S.W. Park, J.W. Lee, P.W. Yu, J.B. Yoo
Tu_P070	EFFECT OF AN ELECTRIC FIELD ON THE ELECTROLUMINESCENCE AND THE PHOTOCURRENT IN InGaN SINGLE QUANTUM WELLS LIGHT EMITTING DIODES P. de Mierry, B. Beaumont, S. Dalmaso, M. Leroux, P. Gibart
Tu_P071	PHOTOLUMINESCENCE DYNAMICS IN STRAINED AlGaIn/GaN QUANTUM WELLS R. Gaska, M.S. Shur, A. Bykhovski, G. Tamulaitis, A. Zukauskas, S. Jursenas, G. Kurilcik, M.A. Khan, J.W. Yang
Tu_P072	OPTICAL CHARACTERISTICS OF AlGaIn, GaN, AND InGaIn THIN FILMS: A COMPARISON AND TEMPERATURE DEPENDENCE Yong-Hoon Cho, T.J. Schmidt, G.H. Gainer, J.B. Lam, J.J. Song, S. Keller, U.K. Mishra, S.P. DenBaars, W. Yang, D.S. Kim, W. Jhe
Tu_P073	MULTIPHONON RESONANT RAMAN SCATTERING IN GaN/Al _x Ga _{1-x} N QUANTUM WELLS F. Demangeot, J. Gleize, J. Frandon, M.A. Renucci, M. Kuball, N. Grandjean, J. Massies
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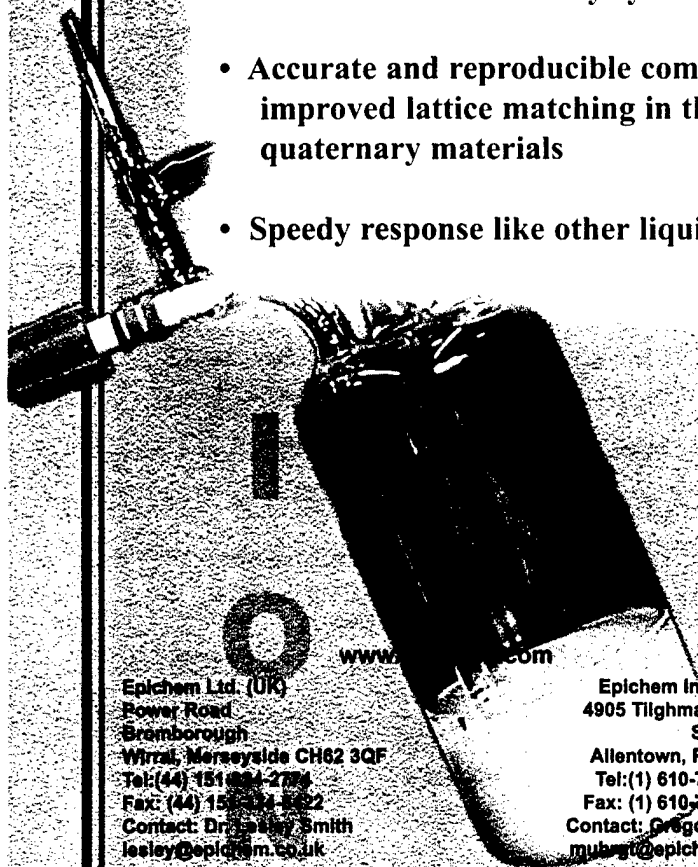
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- Tu_P102** RAMAN MICROSCOPY OF LATERAL EPITAXIAL OVERGROWTH OF GaN ON SAPPHIRE
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D.J. Dugdale, S.K. Pugh, S. Brand, R.A. Abram
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Pierre Bigenwald, Pierre Lefebvre, Thierry Bretagnon, Bernard Gil

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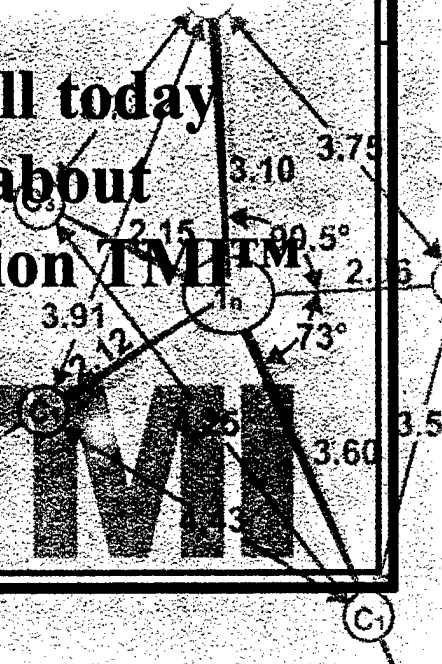


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POSTER SESSION 3

Wednesday July 7th

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- We_P009** QUANTITATIVE MODEL FOR THE MBE - GROWTH OF TERNARY NITRIDES
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- We_P010** STUDY OF INDIUM INCORPORATION INTO InGaIn TERNARY ALLOYS GROWN BY LOW-PRESSURE METALORGANIC VAPOR PHASE EPITAXY (LP-MOVPE)
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- We_P013** GROWTH OF InGaIn ALLOY ON CUBIC GaN BY METALORGANIC VAPOR-PHASE EPITAXY
Atsushi Nakadaira, Hidenao Tanaka
- We_P014** METAL-ORGANIC VAPOR PHASE EPITAXY GROWTH AND PROPERTIES OF GaInNAs BULK AND MULTIPLE QUANTUM WELL STRUCTURES
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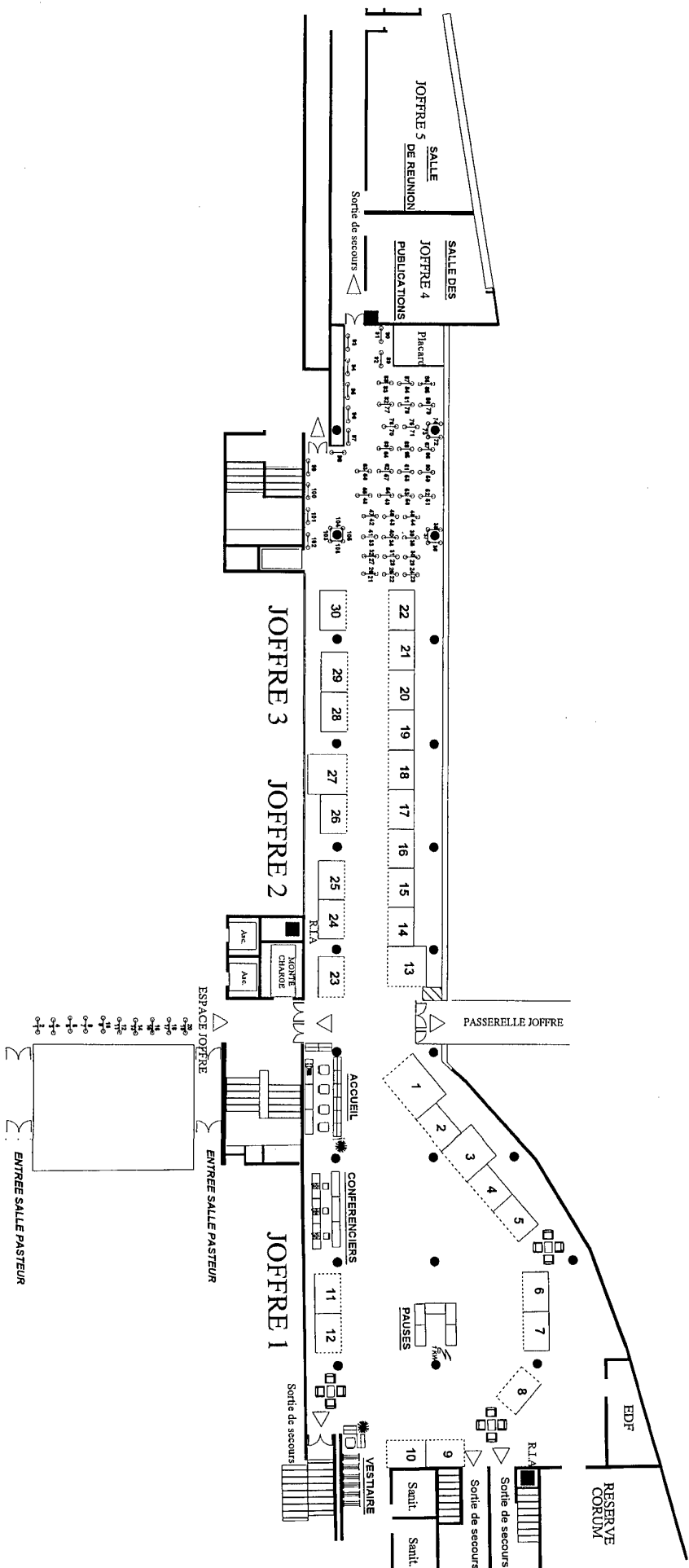
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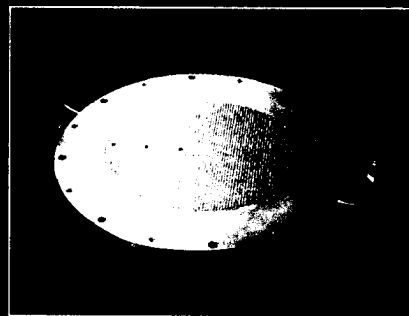
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